N-Channel Silicon MOSFET



2SK1412LS

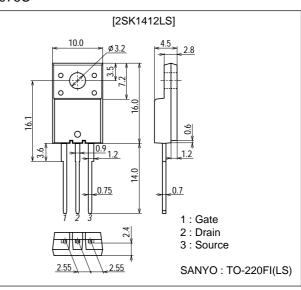
# **Ultrahigh-Speed Switching Applications**

## Features

- · Low ON-resistance, low input capacitance.
- Ultrahigh-speed switching.
- High reliability (Adoption of HVP process).
- Micaless package facilitating mounting.

# Package Dimensions

unit : mm 2078C



# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		1500	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	۱D		0.1	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	0.2	А
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C	20	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	1500			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =1200V, V <sub>GS</sub> =0			100	μA
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0			±100	nA
Ū		V <sub>GS</sub> =±20V, V <sub>DS</sub> =0			±100	

(Note) Be careful in handling the 2SK1412LS because it has no protection diode between gate and source.

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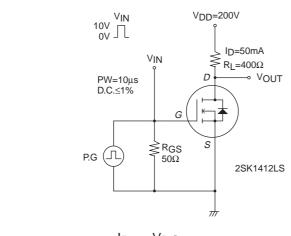
Marking: K1412

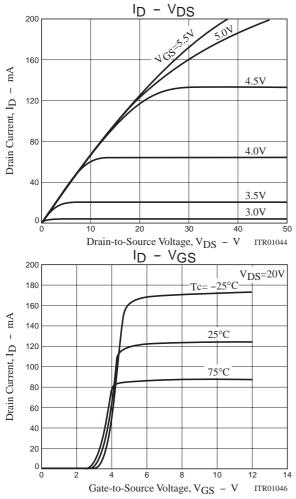
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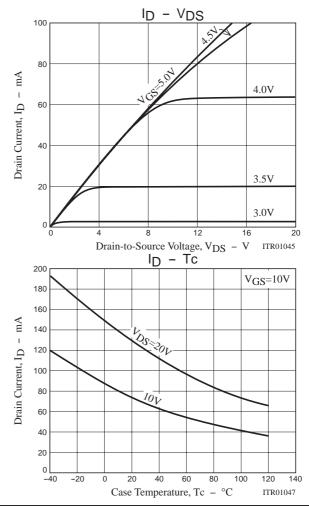
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Continued from preceding page.

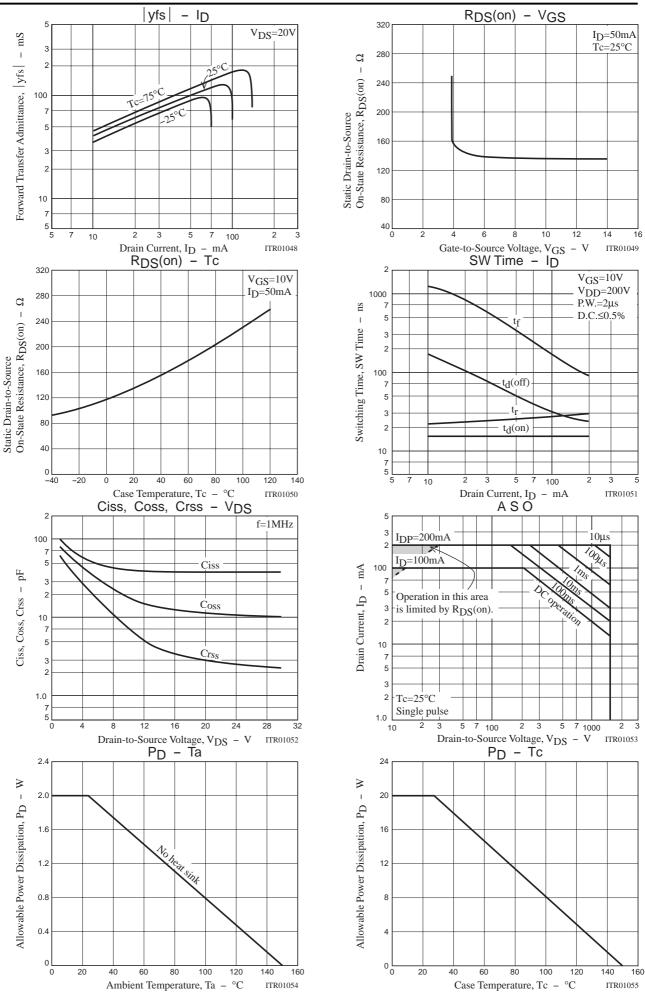
Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.5		3.5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =20V, I <sub>D</sub> =50mA	50	100		mS
Static Drain-to-Source On-State Resistance	RDS(on)	ID=50mA, VGS=10V		140	200	Ω
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		40		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		12		pF
Reverse Transfer Capacitance	Crss	VDS=20V, f=1MHz		3.0		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		15		ns
Rise Time	tr	See specified Test Circuit.		25		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		50		ns
Fall Time	tf	See specified Test Circuit.		350		ns
Diode Forward Voltage	VSD	IS=0.1A, VGS=0		1.0	1.5	V

## Switching Time Test Circuit









No.4228-3/4

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